	(19) (12)		(KR) (A)				
(51) 。Int. Cl. ⁷ H01L 29/78					(11) (43)		2001 - 0077099 2001 08 17
(21) (22)	10 - 2000 - 0004677 2000 01 31						
(71)							
		3	416				
(72)				L G	209	703	
(74)							
:							
(54)							

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2

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2

100: 1 , 102: 104: , 106: 108: , 110: 111: . . (LDD) , 112: 113: , 114: 115: / , 116: 116': , 117: (MOS transistor) (well) Ν Vdd Vss 가 Ρ Ν (well bias) 가 (common ty 가 pe) Ν 가 Ν Ν 가 (latch - up) (ion radiation) 가 (Turn - on) 가 Ν 가 가 2 (per) 1 (well bias contac t)

- 2 -

(10)

(12),

(14),

(well)

1

(18) (16) (10) (26) , N 22 20 가 24 1 (well bias area) 가 22 Vdd가 가 가 22' Vss 가 가 (10) 가 가 가 가 1 가 2 2 (W) (LDD) 1 가 2

- 3 -

1 2000 4000 $0.2 \ 0.8 \mu m$ 1E13 1E15 ions/cm² (CMP: Chemical Mechanical Polishing) 2 (104), (102), (100), (100) (106)(104) (106) (108)가 (110) , (110)(110)(110) (115) , (113) , (108) (114) , (butted contact, 116') (112) (115) (111) (116') (106)(112) 1 1E18 1E20 ions/cm3 (110) (116') / (112) (114)가 가 가

- 4 -

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3
          8
  3
                     P (well)
                                                  (100)
                                                                    (102)
       (104)
                                                  (106)
(104)
            (106)
                    2000 4000
                      (106)
     (106)
                                      (104)
                                                                         (106)
104)
                              2
                                              5E13 1E15 ions/cm<sup>2</sup>
           (100)
                                      (100)
                                                                   (111)
                                                   . . (LDD)
                      . (111)
5
                                                         (全面)
       1000 3000
                                                                         (106)
                                                                                          (10
4)
                       (108)
                                                        (108)가
                                                                               (110)
         2
                        3E15 ions/cm<sup>2</sup>
                       (112)
                                                                       (112)
         (115)
                                  (115)
                                                                          (117)
               (117)
                                          (110)
                                                                                  (113)
                (102)
                                           (115)
              (113)
                                    가
                                           가
    SRAM(Static Random Access Memory)
                                                                       0.2 \ 0.8 \mu m
        (113)
                                                         (115)
                                                                                       (117)
                                                  가
     가
                     (104)
                                                                         (106)
                       (117)
                                                                                      (117)
         (106)
                              (108)
                                         가
               (misalign)
                   (117)
                                                                 1E13 1E15 ions/cm<sup>2</sup>
                     (114)
                                                       가 1E18 1E20 ions/cm
                                  (114)
                                           1
                                (114)
                                                                                 (117)
                                             (全面)
                                                                                         (W)
```

```
(CMP)
 8
                        (116)
                                        (116) (116')
 (106)
                                       (polishing stopper)
                                   가
                                                   (116')가
(116)가
                                                                                   가
             가
                                                 (well bias contact area)
                                 (misalign)
             가
                              (latch - up)
                                                                               가
(57)
      1.
 1
          가
                        2
                                                    2
      2.
 1
      3.
 1
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	2		/		(LDD)	,	
						•	
	4.						
1	,						
			/			4	
			/			1	
	5.						
	J.						
1	,						
					1	1E18 1E20 ions	s/cm³
	6.						
1							
•	,						
		/					
	7.						
	7.						
1	,						
			(W)				
	8.						
1							;
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						2	
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		;					
		가				2	
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9. 8 ,

2000 4000

10.

8 ,

11.8 ,

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12. 8 ,

0.2 0.8μm .

13. 8 ,

14. 8 ,

(CMP)

15.

14 ,

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